TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC74VHC573F,TC74VHC573FT,TC74VHC573FK

Octal D-Type Latch with 3-State Output

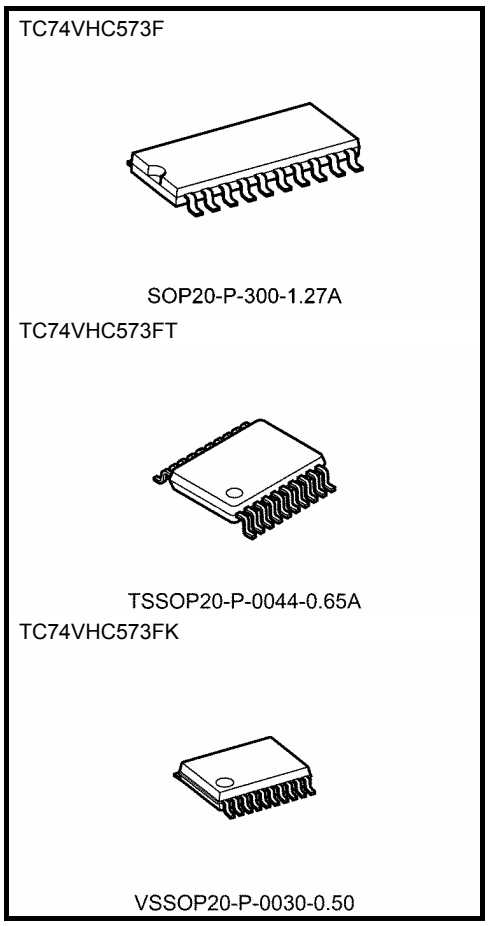
The TC74VHC573 is an advanced high speed CMOS OCTAL LATCH with 3-STATE OUTPUT fabricated with silicon gate C2MOS technology.

It achieves the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

This 8-bit D-type latch is controlled by a latch enable input (LE) and an output enable input ($\overline{OE}$).

When the $\overline{OE}$ input is high, the eight outputs are in a high impedance state.

An input protection circuit ensures that 0 to 5.5 V can be applied to the input pins without regard to the supply voltage. This device can be used to interface 5 V to 3 V systems and two supply systems such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.

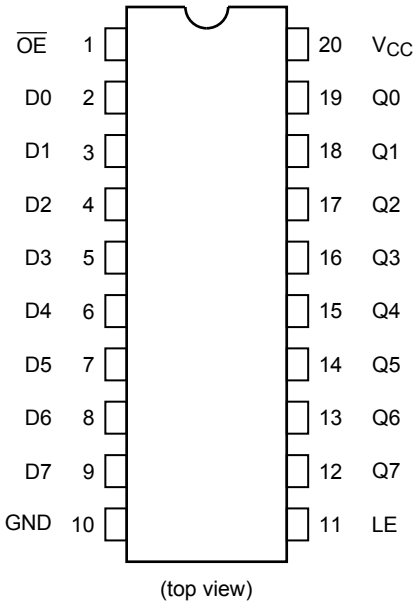


Weight
SOP20-P-300-1.27A : 0.22 g (typ.)
TSSOP20-P-0044-0.65A : 0.08 g (typ.)
VSSOP20-P-0030-0.50 : 0.03 g (typ.)

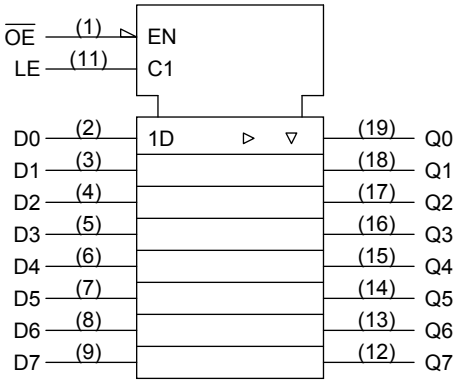
Features

- High speed: t_{pd} = 4.5 ns (typ.) at V_{CC} = 5 V
- Low power dissipation: I_{CC} = 4 μA (max) at Ta = 25°C
- High noise immunity: $V_{NIH} = V_{NIL}$ = 28% V_{CC} (min)
- Power down protection is provided on all inputs.
- Balanced propagation delays: $t_{pLH} \simeq t_{pHL}$
- Wide operating voltage range: $V_{CC\ (opr)}$ = 2 to 5.5 V
- Low noise: V_{OLP} = 1.2 V (max)
- Pin and function compatible with 74ALS573

Pin Assignment



IEC Logic Symbol



Truth Table

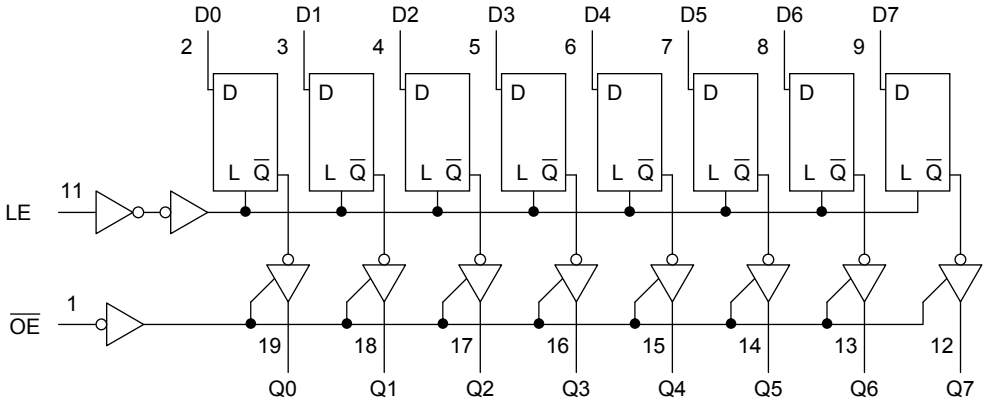
Inputs			Output
$\overline{OE}$	LE	D	
H	X	X	Z
L	L	X	Q_n
L	H	L	L
L	H	H	H

X: Don’t care

Z: High impedance

Q_n: Q outputs are latched at the time when the LE input is taken to a low logic level.

System Diagram



Absolute Maximum Ratings (Note)

Characteristics	Symbol	Rating	Unit
Supply voltage range	V_{CC}	−0.5 to 7.0	V
DC input voltage	V_{IN}	−0.5 to 7.0	V
DC output voltage	V_{OUT}	−0.5 to V_{CC} + 0.5	V
Input diode current	I_{IK}	−20	mA
Output diode current	I_{OK}	±20	mA
DC output current	I_{OUT}	±25	mA
DC V_{CC}/ground current	I_{CC}	±75	mA
Power dissipation	P_D	180	mW
Storage temperature	T_{stg}	−65 to 150	°C

Note: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.
Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook (“Handling Precautions”/“Derating Concept and Methods”) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Operating Ranges (Note)

Characteristics	Symbol	Rating	Unit
Supply voltage	V_{CC}	2.0 to 5.5	V
Input voltage	V_{IN}	0 to 5.5	V
Output voltage	V_{OUT}	0 to V_{CC}	V
Operating temperature	T_{opr}	−40 to 85	°C
Input rise and fall time	dt/dv	0 to 100 (V_{CC} = 3.3 ± 0.3 V) 0 to 20 (V_{CC} = 5 ± 0.5 V)	ns/V

Note: The operating ranges must be maintained to ensure the normal operation of the device.
Unused inputs must be tied to either VCC or GND.

Electrical Characteristics

DC Characteristics

Characteristics	Symbol	Test Condition		V_{CC} (V)	Ta = 25°C Min	Ta = 25°C Typ.	Ta = 25°C Max	Ta = −40 to 85°C Min	Ta = −40 to 85°C Max	Unit
High-level input voltage	V_{IH}	—		2.0	1.50	—	—	1.50	—	V
				3.0 to 5.5	V_{CC} × 0.7	—	—	V_{CC} × 0.7	—	
Low-level input voltage	V_{IL}	—		2.0	—	—	0.50	—	0.50	V
				3.0 to 5.5	—	—	V_{CC} × 0.3	—	V_{CC} × 0.3	
High-level output voltage	V_{OH}	V_{IN} = V_{IH} or V_{IL}	I_{OH} = −50 μA	2.0	1.9	2.0	—	1.9	—	V
				3.0	2.9	3.0	—	2.9	—	
				4.5	4.4	4.5	—	4.4	—	
			I_{OH} = −4 mA	3.0	2.58	—	—	2.48	—	
			I_{OH} = −8 mA	4.5	3.94	—	—	3.80	—	
Low-level output voltage	V_{OL}	V_{IN} = V_{IH} or V_{IL}	I_{OL} = 50 μA	2.0	—	0.0	0.1	—	0.1	V
				3.0	—	0.0	0.1	—	0.1	
				4.5	—	0.0	0.1	—	0.1	
			I_{OL} = 4 mA	3.0	—	—	0.36	—	0.44	
			I_{OL} = 8 mA	4.5	—	—	0.36	—	0.44	
3-state output off-state current	I_{OZ}	V_{IN} = V_{IH} or V_{IL} V_{OUT} = V_{CC} or GND		5.5	—	—	±0.25	—	±2.50	μA
Input leakage current	I_{IN}	V_{IN} = 5.5 V or GND		0 to 5.5	—	—	±0.1	—	±1.0	μA
Quiescent supply current	I_{CC}	V_{IN} = V_{CC} or GND		5.5	—	—	4.0	—	40.0	μA

Timing Requirements (input: $t_r = t_f = 3$ ns)

Characteristics	Symbol	Test Condition	V_{CC} (V)	Ta = 25°C Typ.	Ta = 25°C Limit	Ta = −40 to 85°C Limit	Unit
Minimum pulse width (LE)	$t_{w\,(H)}$	—	3.3 ± 0.3	—	5.0	5.0	ns
			5.0 ± 0.5	—	5.0	5.0	
Minimum set-up time	t_s	—	3.3 ± 0.3	—	3.5	3.5	ns
			5.0 ± 0.5	—	3.5	3.5	
Minimum hold time	t_h	—	3.3 ± 0.3	—	1.5	1.5	ns
			5.0 ± 0.5	—	1.5	1.5	

AC Characteristics (input: $t_r = t_f = 3$ ns)

Characteristics	Symbol	Test Condition			Ta = 25°C			Ta = −40 to 85°C		Unit
			V_{CC} (V)	C_L (pF)	Min	Typ.	Max	Min	Max	
Propagation delay time (LE-Q)	t_{pLH} t_{pHL}	—	3.3 ± 0.3	15	—	7.6	11.9	1.0	14.0	ns
				50	—	10.1	15.4	1.0	17.5	
			5.0 ± 0.5	15	—	5.0	7.7	1.0	9.0	
				50	—	6.5	9.7	1.0	11.0	
Propagation delay time (D-Q)	t_{pLH} t_{pHL}	—	3.3 ± 0.3	15	—	7.0	11.0	1.0	13.0	ns
				50	—	9.5	14.5	1.0	16.5	
			5.0 ± 0.5	15	—	4.5	6.8	1.0	8.0	
				50	—	6.0	8.8	1.0	10.0	
3-state output enable time	t_{pZL} t_{pZH}	R_L = 1 kΩ	3.3 ± 0.3	15	—	7.3	11.5	1.0	13.5	ns
				50	—	9.8	15.0	1.0	17.0	
			5.0 ± 0.5	15	—	5.2	7.7	1.0	9.0	
				50	—	6.7	9.7	1.0	11.0	
3-state output disable time	t_{pLZ} t_{pHZ}	R_L = 1 kΩ	3.3 ± 0.3	50	—	10.7	14.5	1.0	16.5	ns
			5.0 ± 0.5	50	—	6.7	9.7	1.0	11.0	
Output to output skew	t_{osLH} t_{osHL}	(Note 1)	3.3 ± 0.3	50	—	—	1.5	—	1.5	ns
			5.0 ± 0.5	50	—	—	1.0	—	1.0	
Input capacitance	C_{IN}	—			—	4	10	—	10	pF
Output capacitance	C_{OUT}	—			—	6	—	—	—	pF
Power dissipation capacitance	C_{PD}	(Note 2)			—	29	—	—	—	pF

Note 1: Parameter guaranteed by design.

$t_{osLH} = |t_{pLHm} - t_{pLHn}|$, $t_{osHL} = |t_{pHLm} - t_{pHLn}|$

Note 2: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

$I_{CC\ (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8$ (per latch)

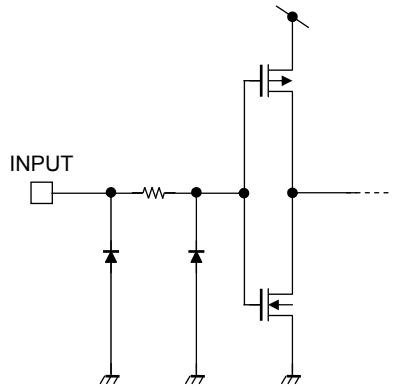
And the total C_{PD} when n pcs. of latch operate can be gained by the following equation:

C_{PD} (total) = 21 + 8·n

Noise Characteristics (input: $t_r = t_f = 3$ ns)

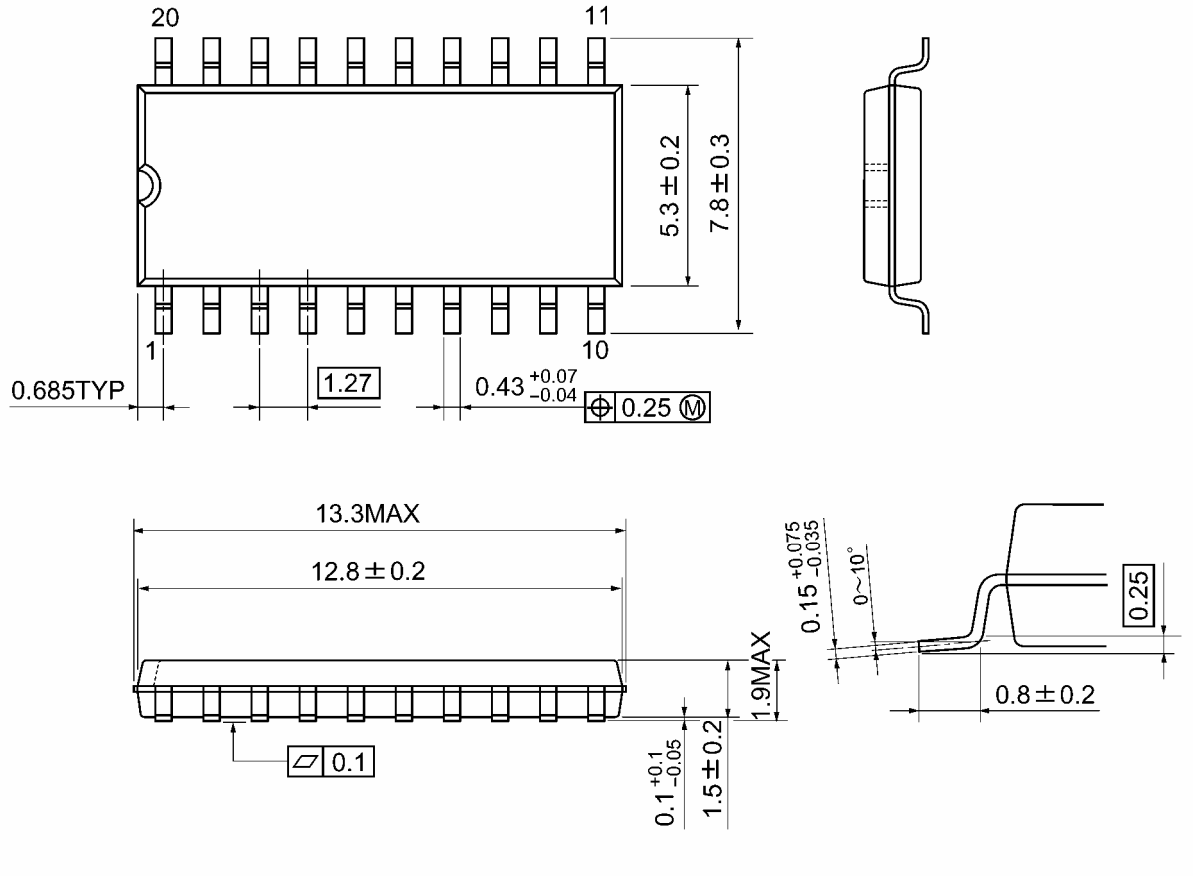
Characteristics	Symbol	Test Condition	Ta = 25°C		Unit
		V_{CC} (V)	Typ.	Max	
Quiet output maximum dynamic V_{OL}	V_{OLP}	C_L = 50 pF	5.0	0.8	1.0	V
Quiet output minimum dynamic V_{OL}	V_{OLV}	C_L = 50 pF	5.0	−0.8	−1.0	V
Minimum high level dynamic input voltage	V_{IHD}	C_L = 50 pF	5.0	—	3.5	V
Maximum low level dynamic input voltage	V_{ILD}	C_L = 50 pF	5.0	—	1.5	V

Input Equivalent Circuit



Package Dimensions

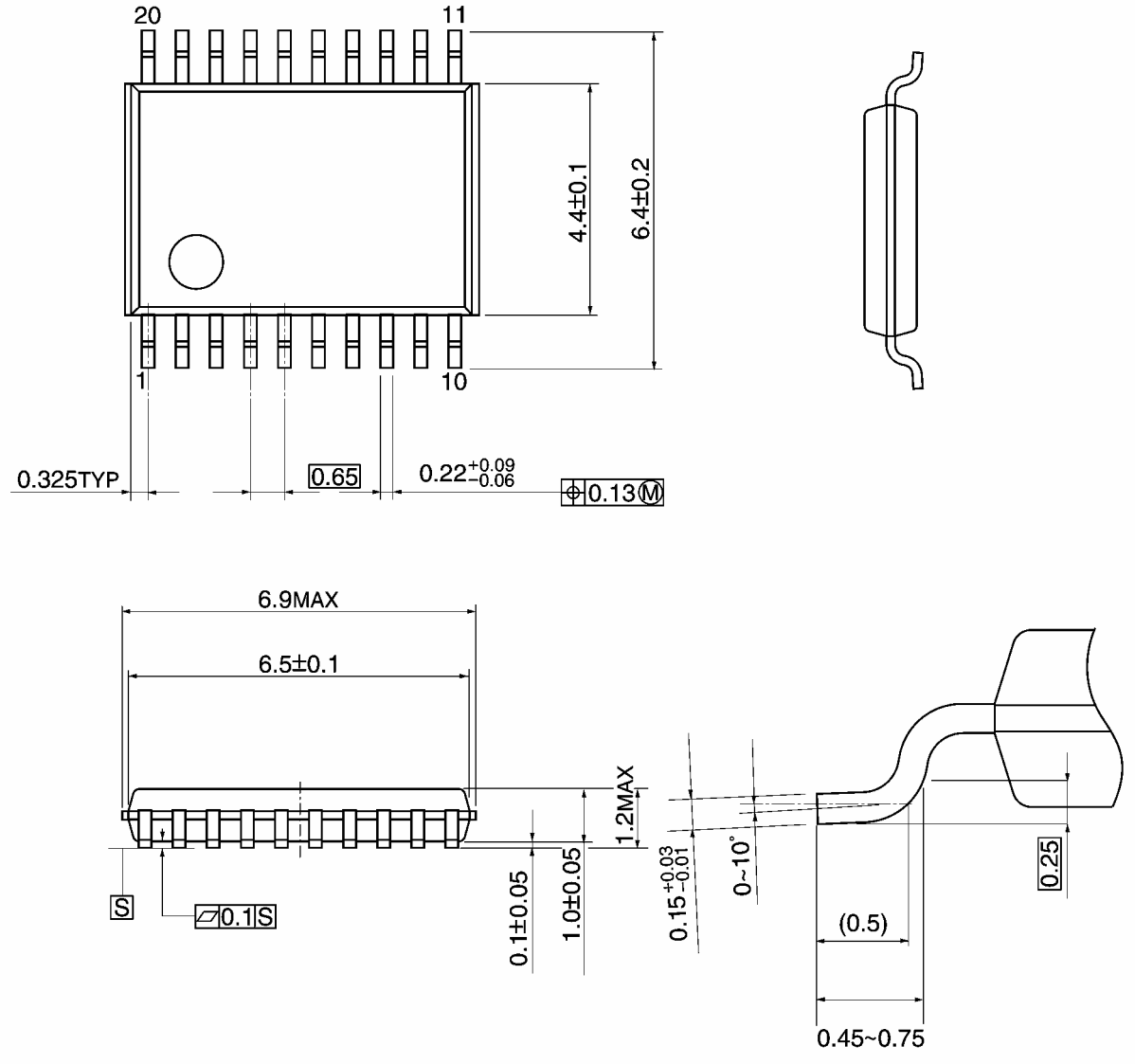
SOP20-P-300-1.27A Unit: mm



Weight: 0.22 g (typ.)

Package Dimensions

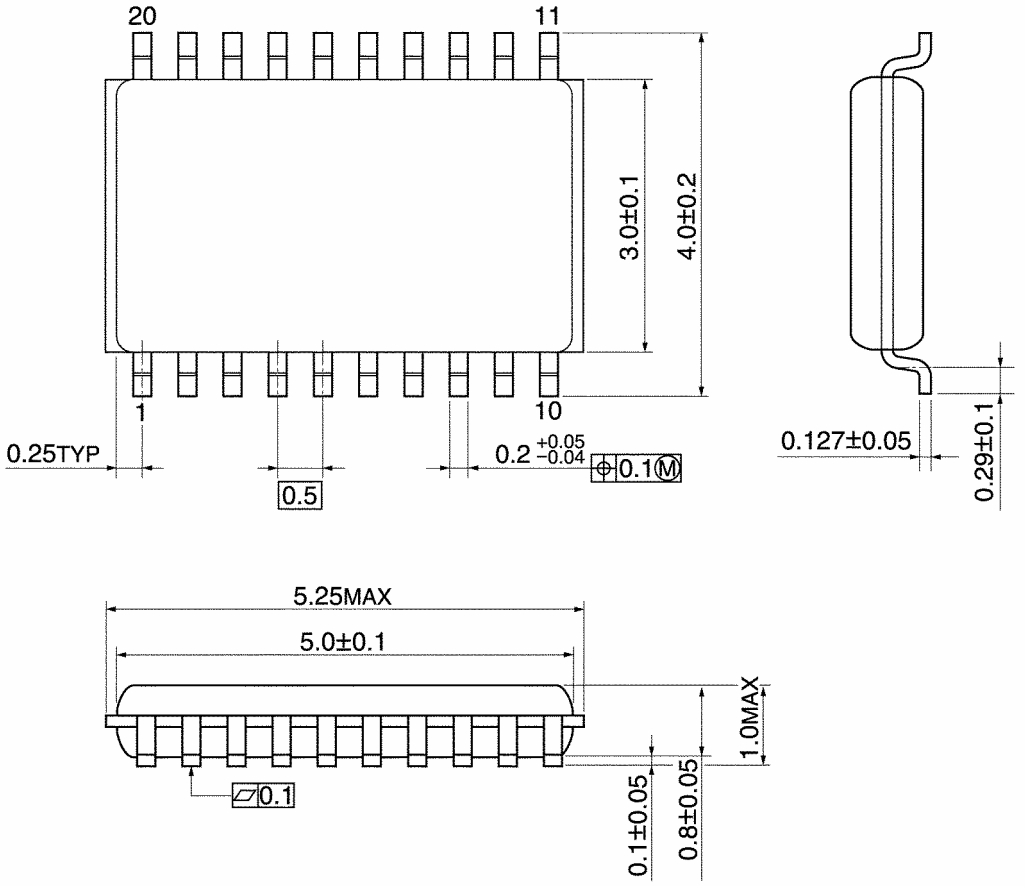
TSSOP20-P-0044-0.65A Unit: mm



Weight: 0.08 g (typ.)

Package Dimensions

VSSOP20-P-0030-0.50 Unit: mm



Weight: 0.03 g (typ.)

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